

# BUK7Y12-55B

## N-channel TrenchMOS standard level FET

Rev. 03 — 7 April 2010

Product data sheet

## 1. Product profile

### 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using NXP High-Performance Automotive (HPA) TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 1.2 Features and benefits

- Q101 compliant
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

### 1.3 Applications

- 12 V and 24 V loads
- Advanced braking systems (ABS)
- Automotive systems
- General purpose power switching
- Motors, lamps and solenoids

### 1.4 Quick reference data

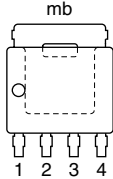
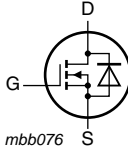
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$	-	-	55	V
$I_D$	drain current	$V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 1</a> ; see <a href="#">Figure 4</a>	-	-	61.8	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>	-	-	105	W
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$ ; $I_D = 20\text{ A}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 13</a> ; see <a href="#">Figure 12</a>	-	8.2	12	m $\Omega$
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 61.8\text{ A}$ ; $V_{sup} \leq 55\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ °C}$ ; unclamped	-	-	129	mJ
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$I_D = 20\text{ A}$ ; $V_{DS} = 44\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; see <a href="#">Figure 14</a>	-	14.8	-	nC



## 2. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p style="text-align: center;"><b>SOT669 (LFPAK)</b></p>	 <p style="text-align: center;"><i>mbb076</i></p>
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

## 3. Ordering information

**Table 3. Ordering information**

Type number	Package		Version
	Name	Description	
BUK7Y12-55B	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

## 4. Limiting values

**Table 4. Limiting values**

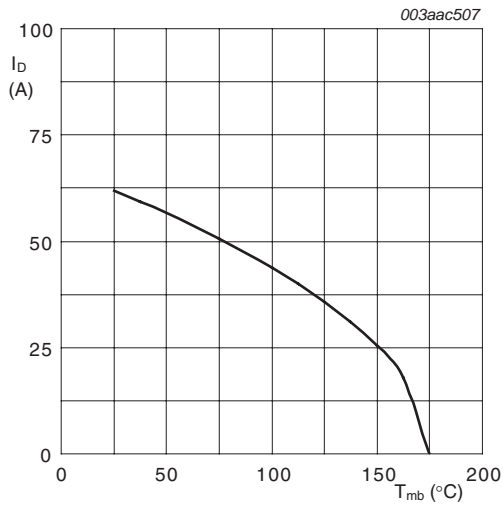
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$	-	-	55	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	-	55	V
$V_{GS}$	gate-source voltage		-20	-	20	V
$I_D$	drain current	$T_{mb} = 25\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; see <a href="#">Figure 1</a> ; see <a href="#">Figure 4</a>	-	-	61.8	A
		$T_{mb} = 100\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; see <a href="#">Figure 1</a>	-	-	43.7	A
$I_{DM}$	peak drain current	$T_{mb} = 25\text{ °C}$ ; $t_p \leq 10\text{ }\mu\text{s}$ ; pulsed; see <a href="#">Figure 4</a>	-	-	247	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>	-	-	105	W
$T_{stg}$	storage temperature		-55	-	175	°C
$T_j$	junction temperature		-55	-	175	°C
<b>Source-drain diode</b>						
$I_S$	source current	$T_{mb} = 25\text{ °C}$	-	-	61.8	A
$I_{SM}$	peak source current	$t_p \leq 10\text{ }\mu\text{s}$ ; pulsed; $T_{mb} = 25\text{ °C}$	-	-	247	A
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 61.8\text{ A}$ ; $V_{sup} \leq 55\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ °C}$ ; unclamped	-	-	129	mJ
$E_{DS(AL)R}$	repetitive drain-source avalanche energy	see <a href="#">Figure 3</a>	<a href="#">[1]</a> <a href="#">[2]</a> <a href="#">[3]</a>	-	-	J

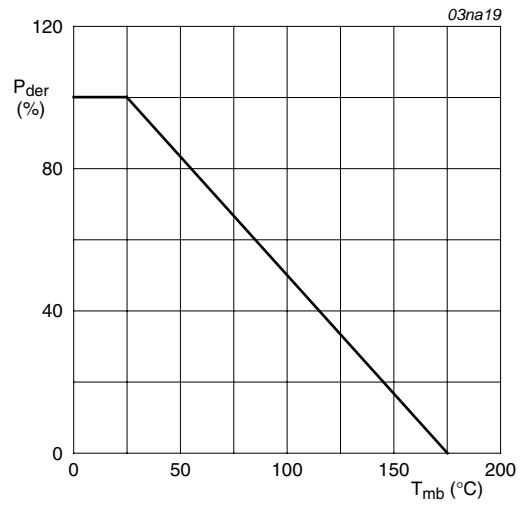
[1] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[2] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

[3] Refer to application note AN10273 for further information.

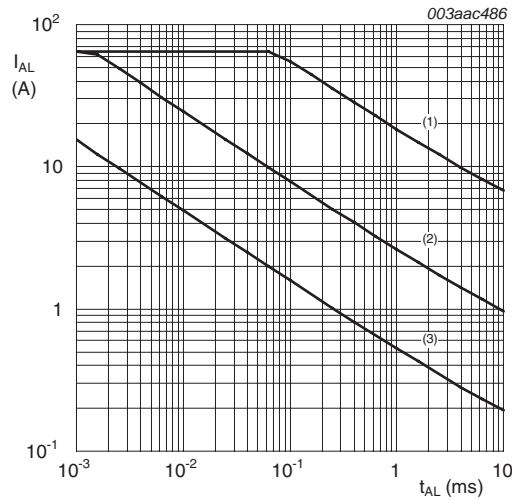


**Fig 1. Continuous drain current as a function of mounting base temperature**



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

**Fig 2. Normalized total power dissipation as a function of mounting base temperature**



**Fig 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time**

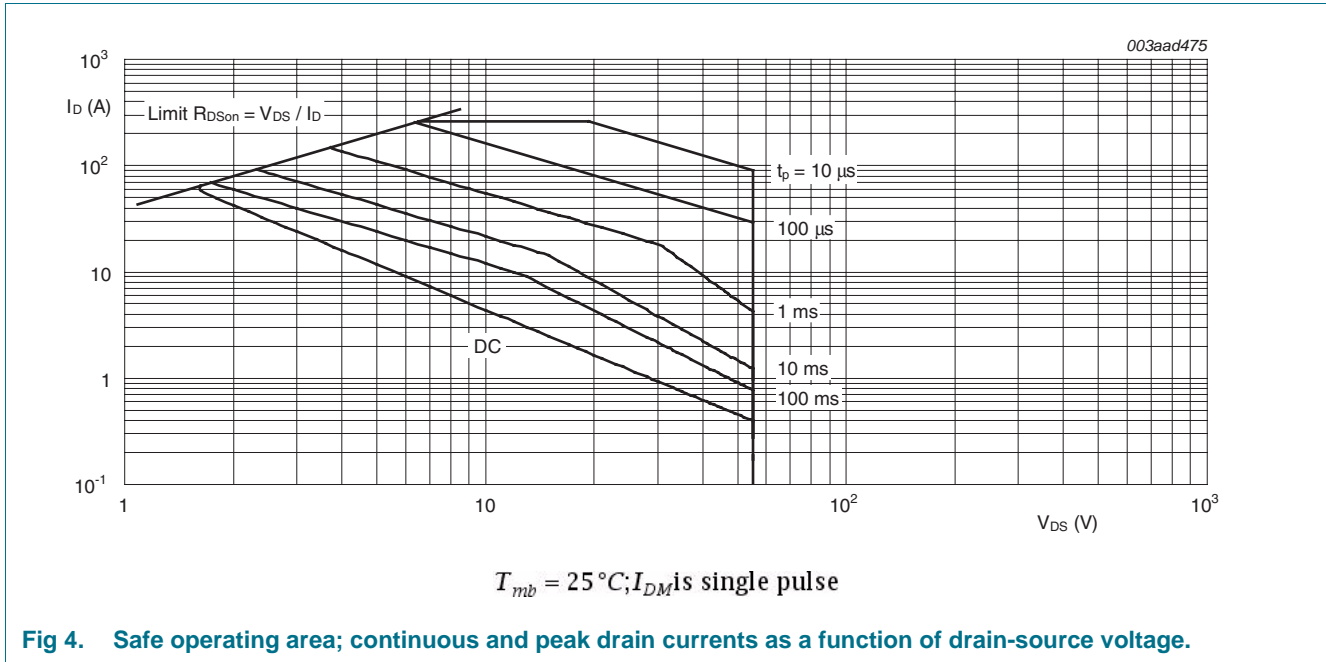


Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 5</a>	-	-	1.42	K/W

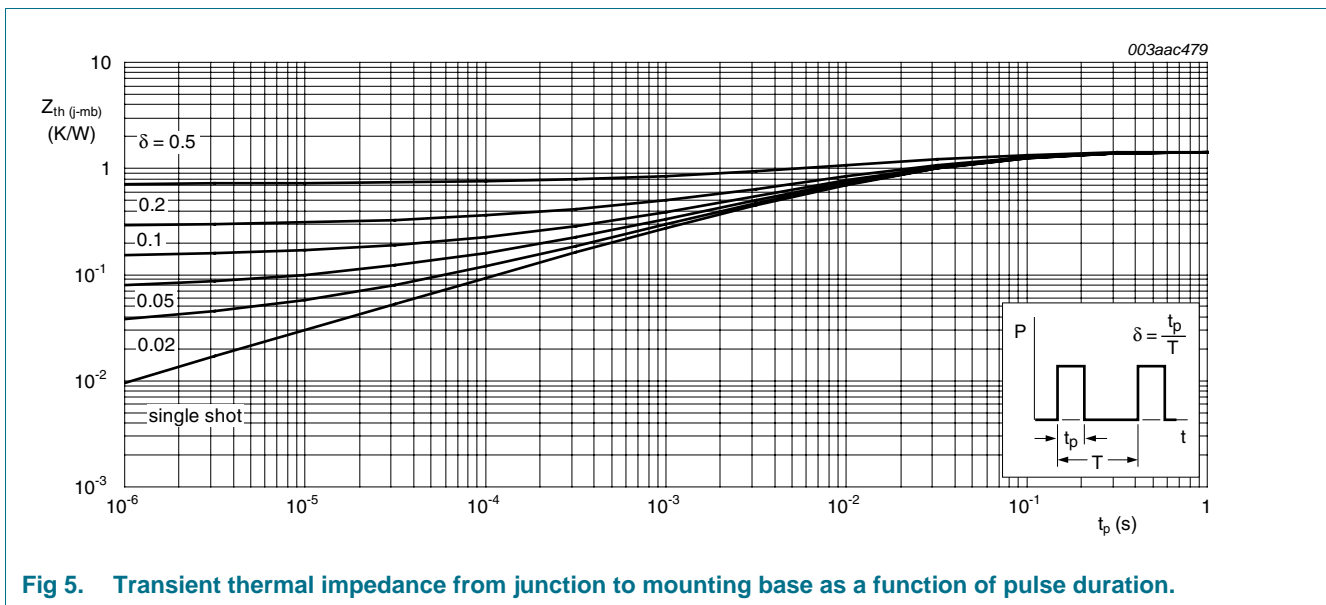
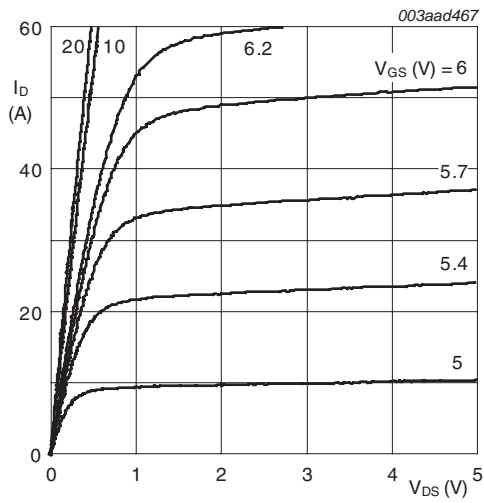


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration.

## 6. Characteristics

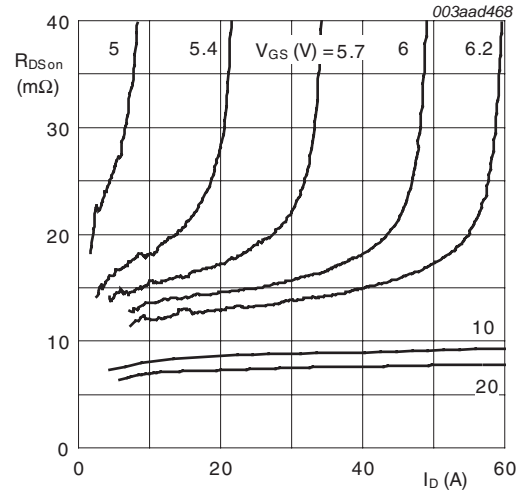
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	55	-	-	V
		$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	50	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 10</a> ; see <a href="#">Figure 11</a>	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see <a href="#">Figure 10</a>	-	-	4.4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see <a href="#">Figure 10</a>	1	-	-	V
$I_{DSS}$	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.02	1	$\mu\text{A}$
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$	-	-	500	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
		$V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ see <a href="#">Figure 12</a> ; see <a href="#">Figure 13</a>	-	-	27.6	m $\Omega$
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 13</a> ; see <a href="#">Figure 12</a>	-	8.2	12	m $\Omega$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 20 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$ see <a href="#">Figure 14</a>	-	35.2	-	nC
$Q_{GS}$	gate-source charge		-	9.24	-	nC
$Q_{GD}$	gate-drain charge		-	14.8	-	nC
$C_{iss}$	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 15</a>	-	1550	2067	pF
$C_{oss}$	output capacitance		-	328	394	pF
$C_{rss}$	reverse transfer capacitance		-	153	210	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.5 \text{ } \Omega; V_{GS} = 10 \text{ V};$ $R_{G(ext)} = 10 \text{ } \Omega$	-	19.3	-	ns
$t_r$	rise time		-	29.4	-	ns
$t_{d(off)}$	turn-off delay time		-	43.2	-	ns
$t_f$	fall time		-	22	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 25 \text{ V}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 16</a>	-	0.85	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 20 \text{ A}; di_S/dt = -100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V};$ $V_{DS} = 30 \text{ V}$	-	45	-	ns
$Q_r$	recovered charge		-	84	-	nC



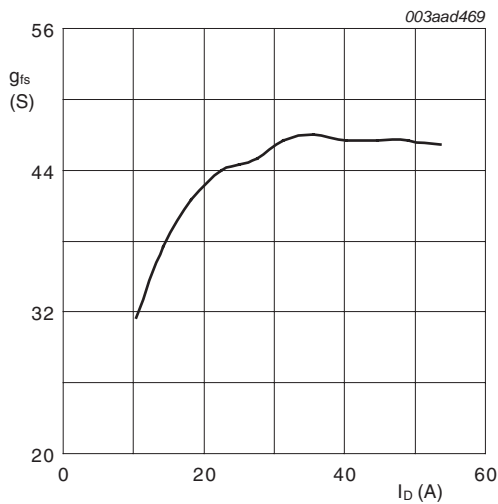
$T_j = 25^\circ\text{C}$

**Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values.**



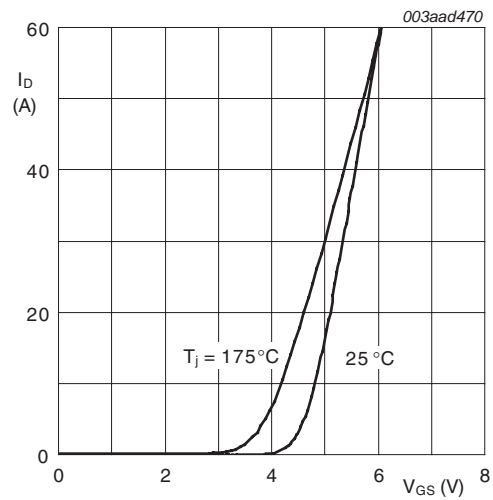
$T_j = 25^\circ\text{C}$

**Fig 7. Drain-source on-state resistance as a function of drain current; typical values.**



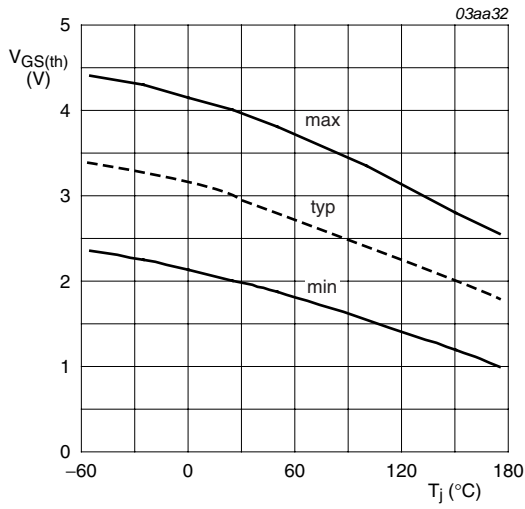
$T_j = 25^\circ\text{C}; V_{DS} = 25\text{V}$

**Fig 8. Forward transconductance as a function of drain current; typical values.**



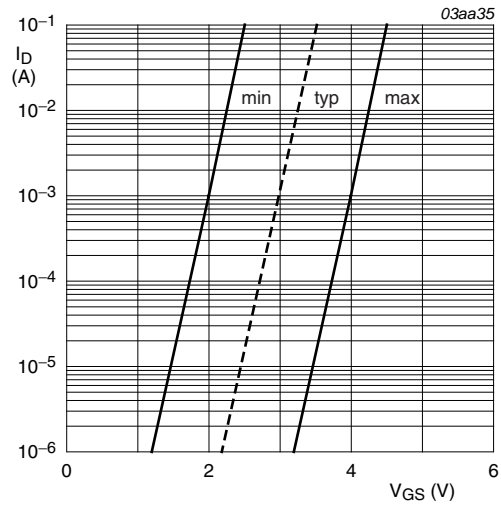
$V_{DS} = 25\text{V}$

**Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values.**



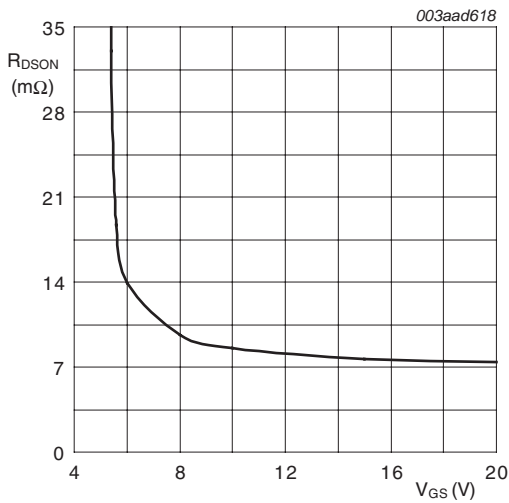
$$I_D = 1\text{mA}; V_{DS} = V_{GS}$$

**Fig 10. Gate-source threshold voltage as a function of junction temperature**



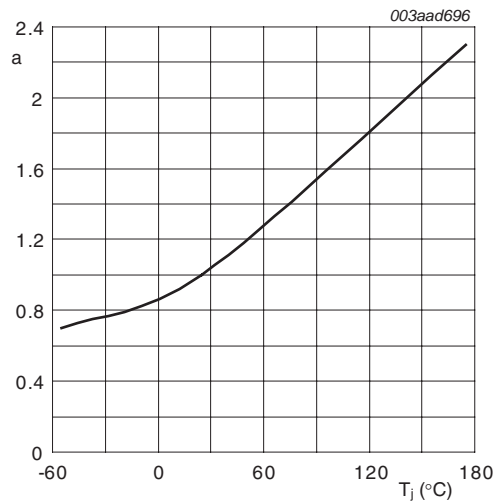
$$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 5\text{V}$$

**Fig 11. Sub-threshold drain current as a function of gate-source voltage**



$$T_j = 25\text{ }^\circ\text{C}; I_D = 20\text{A}$$

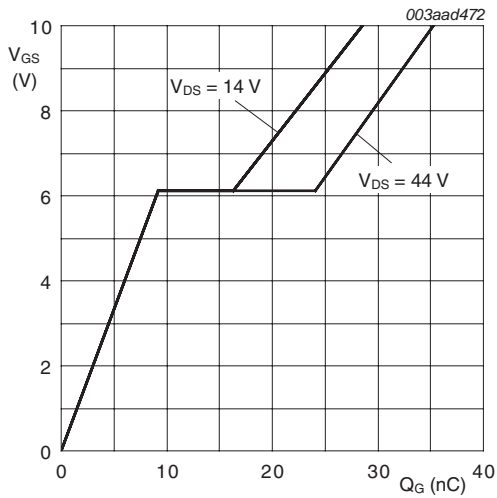
**Fig 12. Drain-source on-state resistance as a function of gate-source voltage; typical values.**



$$a = \frac{R_{DS(on)}}{R_{DS(on)@25^\circ\text{C}}}$$

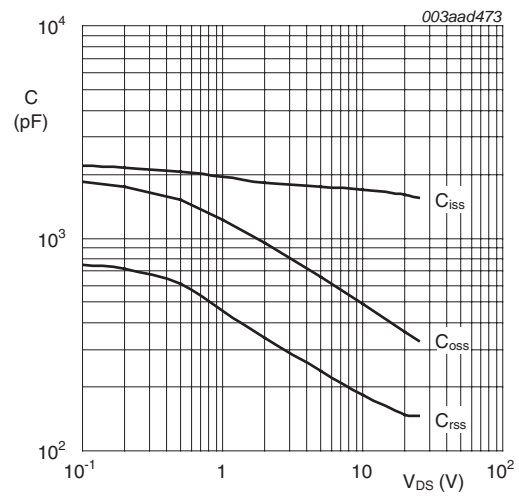
**Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature.**





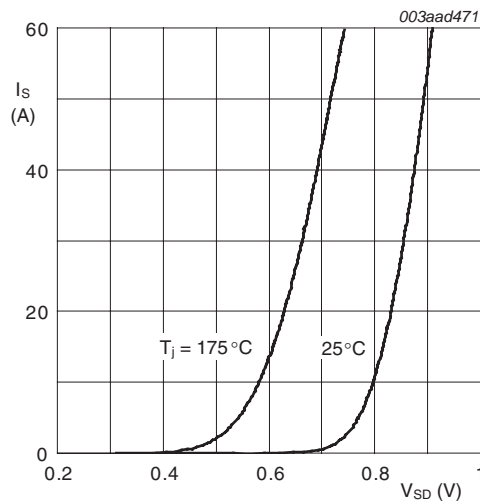
$T_j = 25^\circ\text{C}; I_D = 20\text{A}$

**Fig 14. Gate-source voltage as a function of gate charge; typical values.**



$V_{GS} = 0\text{V}; f = 1\text{MHz}$

**Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.**



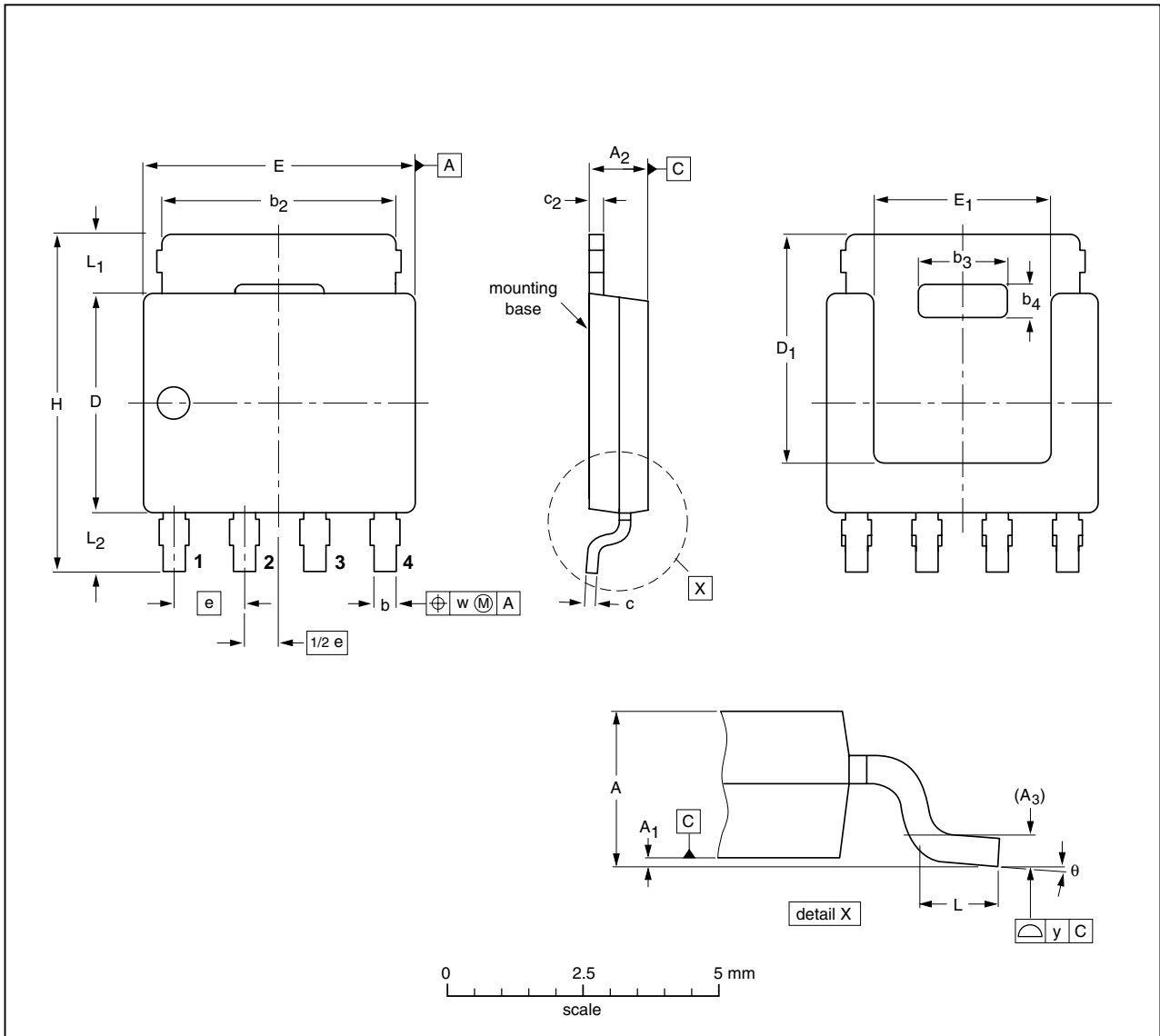
$V_{GS} = 0\text{V}$

**Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values.**

**7. Package outline**

Plastic single-ended surface-mounted package (LFPAK); 4 leads

SOT669



**DIMENSIONS** (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	b	b <sub>2</sub>	b <sub>3</sub>	b <sub>4</sub>	c	c <sub>2</sub>	D <sup>(1)</sup>	D <sub>1</sub> <sup>(1)</sup> <sub>max</sub>	E <sup>(1)</sup>	E <sub>1</sub> <sup>(1)</sup>	e	H	L	L <sub>1</sub>	L <sub>2</sub>	w	y	θ
mm	1.20 1.01	0.15 0.00	1.10 0.95	0.25	0.50 0.35	4.41 3.62	2.2 2.0	0.9 0.7	0.25 0.19	0.30 0.24	4.10 3.80	4.20	5.0 4.8	3.3 3.1	1.27	6.2 5.8	0.85 0.40	1.3 0.8	1.3 0.8	0.25	0.1	8° 0°

**Note**

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT669		MO-235				04-10-13 06-03-16

**Fig 17. Package outline SOT669 (LFPAK)**

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7Y12-55B_3	20100407	Product data sheet	-	BUK7Y12-55B_2
Modifications:	• Status changed from objective to product.			
BUK7Y12-55B_2	20100218	Objective data sheet	-	BUK7Y12-55B_1

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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## 11. Contents

<b>1</b>	<b>Product profile</b> . . . . .	<b>1</b>
1.1	General description . . . . .	1
1.2	Features and benefits . . . . .	1
1.3	Applications . . . . .	1
1.4	Quick reference data . . . . .	1
<b>2</b>	<b>Pinning information</b> . . . . .	<b>2</b>
<b>3</b>	<b>Ordering information</b> . . . . .	<b>2</b>
<b>4</b>	<b>Limiting values</b> . . . . .	<b>3</b>
<b>5</b>	<b>Thermal characteristics</b> . . . . .	<b>5</b>
<b>6</b>	<b>Characteristics</b> . . . . .	<b>6</b>
<b>7</b>	<b>Package outline</b> . . . . .	<b>10</b>
<b>8</b>	<b>Revision history</b> . . . . .	<b>11</b>
<b>9</b>	<b>Legal information</b> . . . . .	<b>12</b>
9.1	Data sheet status . . . . .	12
9.2	Definitions . . . . .	12
9.3	Disclaimers . . . . .	12
9.4	Trademarks . . . . .	13
<b>10</b>	<b>Contact information</b> . . . . .	<b>13</b>

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